



<IGBT Modules>

CM225DX-34T/CM225DXP-34T

HIGH POWER SWITCHING USE
INSULATED TYPE

| | |
|---|--|
|  <p>DX</p> | <p>Collector current I_C 225 A Collector-emitter voltage V_{CES} 1700 V Maximum junction temperature T_{vjmax} 175 °C</p> <ul style="list-style-type: none"> • Flat base type • Copper base plate (Nickel-plating) • RoHS Directive compliant • Tin-plating pin terminals |
|  <p>DXP</p> | <p>Collector current I_C 225 A Collector-emitter voltage V_{CES} 1700 V Maximum junction temperature T_{vjmax} 175 °C</p> <ul style="list-style-type: none"> • Flat base type • Copper base plate (Nickel-plating) • RoHS Directive compliant • Tin-plating pressfit terminals |
| <p style="text-align: center;">dual switch (half-bridge)</p> <ul style="list-style-type: none"> • UL Recognized under UL1557, File No. E323585 | |

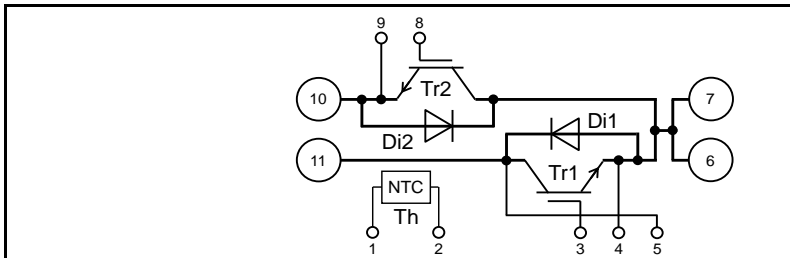
APPLICATION

AC Motor Control, Motion/Servo Control, Power supply, etc.

OPTION (Below options are available.)

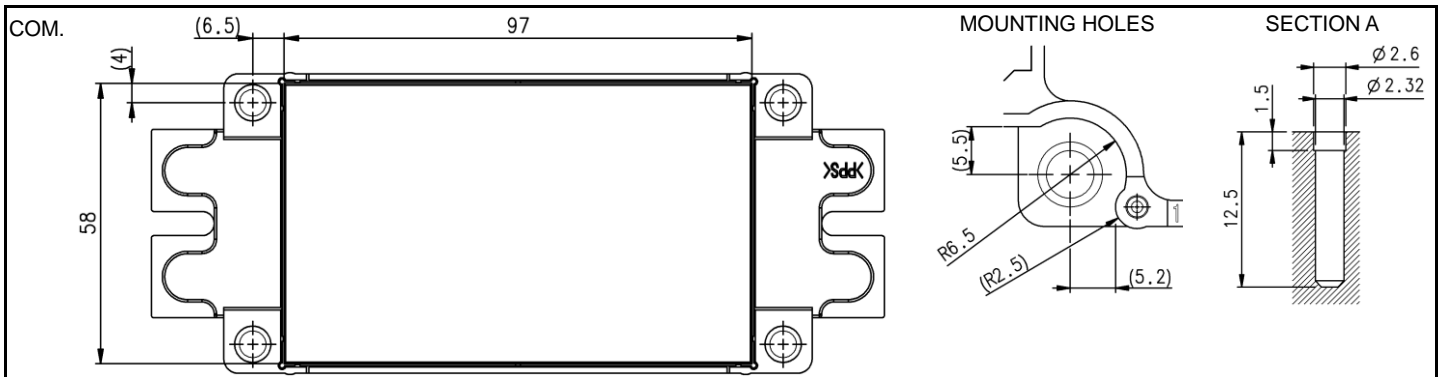
- PC-TIM (Phase Change Thermal Interface Material) pre-apply
- V_{CEsat} selection for parallel connection

INTERNAL CONNECTION



TERMINAL CODE

- | | |
|--------|---------|
| 1. TH1 | 6. C2E1 |
| 2. TH2 | 7. C2E1 |
| 3. G1 | 8. G2 |
| 4. Es1 | 9. Es2 |
| 5. Cs1 | 10. E2 |
| | 11. C1 |



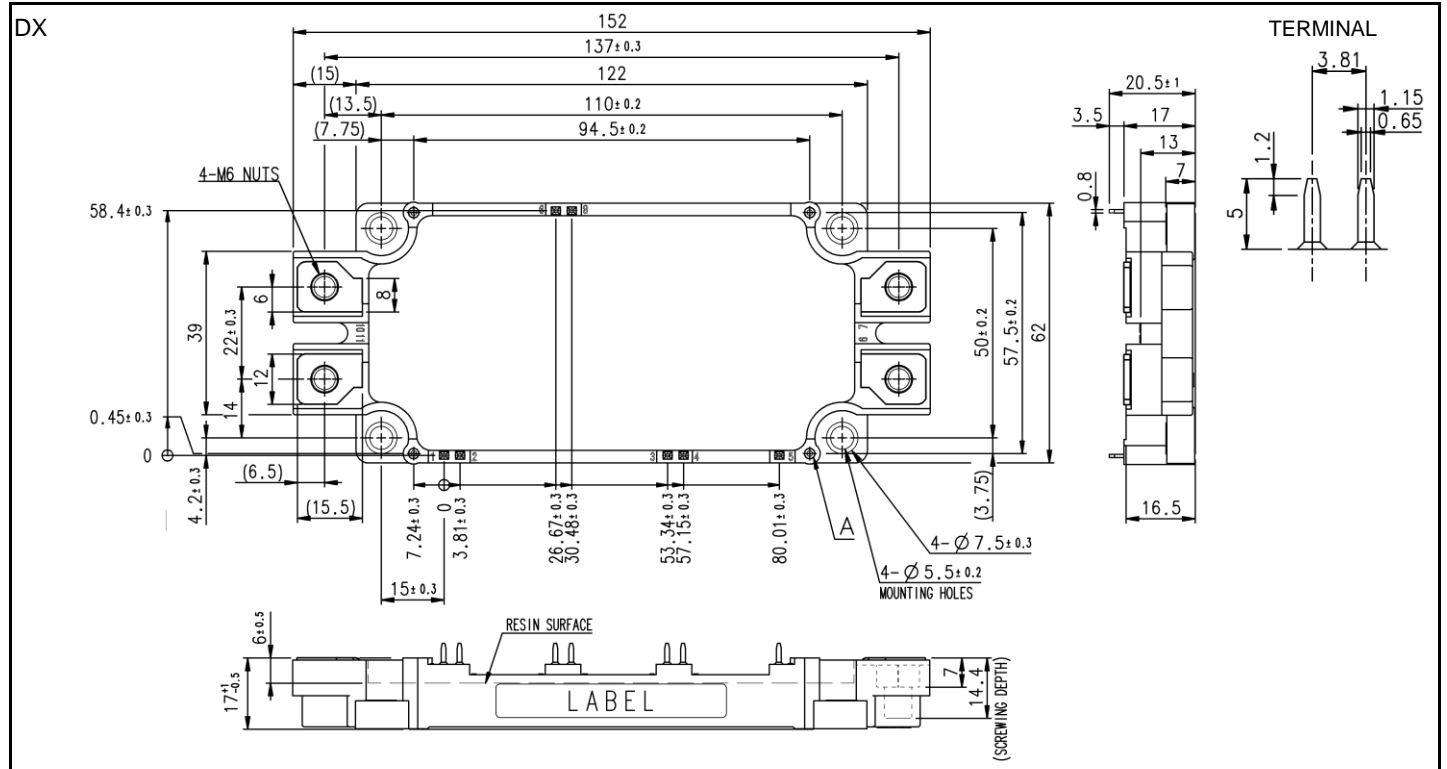
CM225DX-34T/CM225DXP-34T

HIGH POWER SWITCHING USE

INSULATED TYPE

OUTLINE DRAWING

Dimension in mm



Tolerance otherwise specified

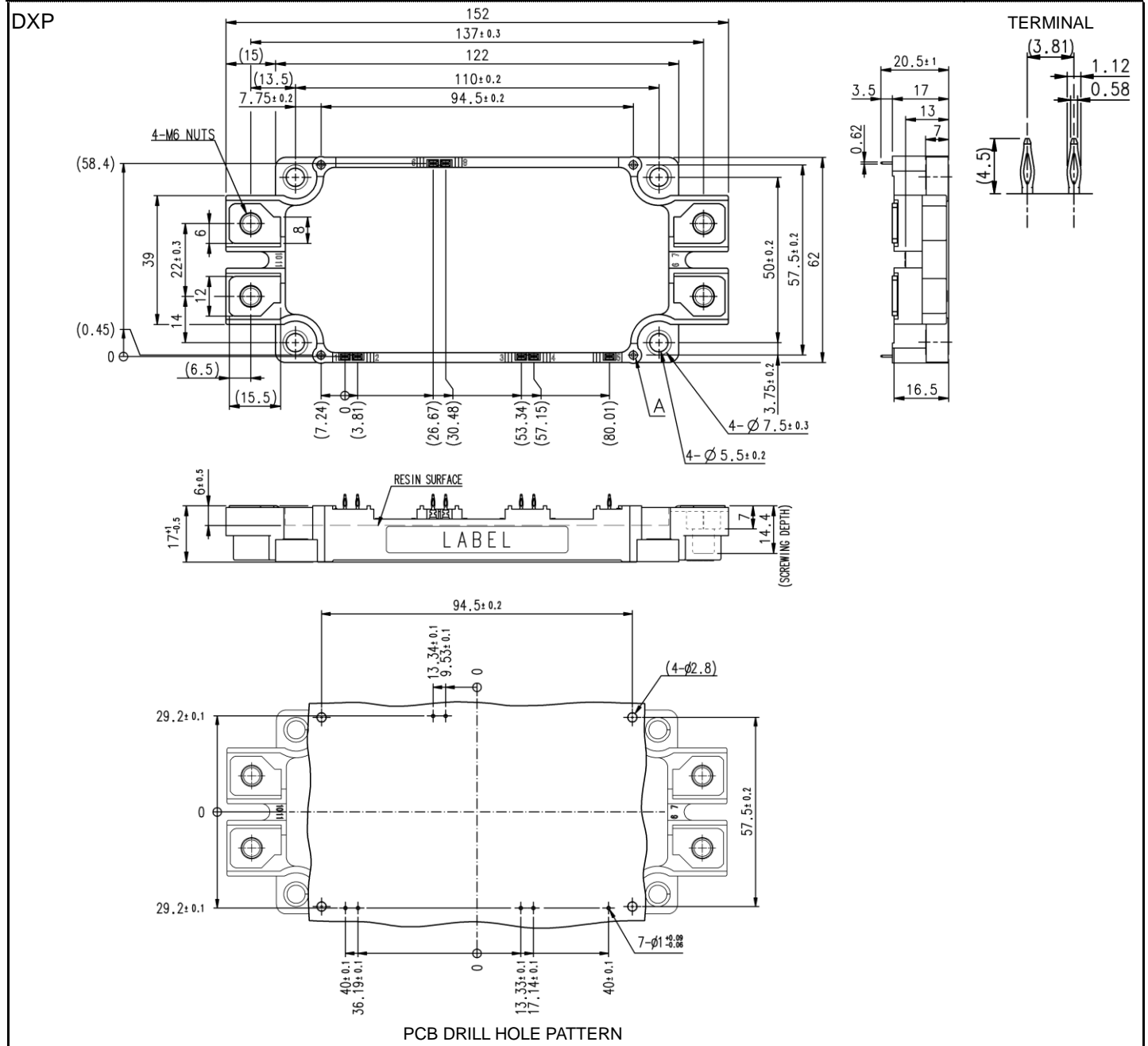
| Division of Dimension | Tolerance |
|-----------------------|-----------|
| 0.5 to 3 | ±0.2 |
| over 3 to 6 | ±0.3 |
| over 6 to 30 | ±0.5 |
| over 30 to 120 | ±0.8 |
| over 120 to 400 | ±1.2 |

CM225DX-34T/CM225DXP-34T

HIGH POWER SWITCHING USE
INSULATED TYPE

OUTLINE DRAWING

Dimension in mm



Tolerance otherwise specified

| Division of Dimension | Tolerance |
|-----------------------|-----------|
| 0.5 to 3 | ±0.2 |
| over 3 to 6 | ±0.3 |
| over 6 to 30 | ±0.5 |
| over 30 to 120 | ±0.8 |
| over 120 to 400 | ±1.2 |

CM225DX-34T/CM225DXP-34T

HIGH POWER SWITCHING USE
INSULATED TYPEMAXIMUM RATINGS ($T_{vj}=25\text{ }^{\circ}\text{C}$, unless otherwise specified)

INVERTER PART IGBT/FWD

| Symbol | Item | Conditions | Rating | Unit |
|-------------------|---------------------------|--|----------|------|
| V_{CES} | Collector-emitter voltage | G-E short-circuited | 1700 | V |
| V_{GES} | Gate-emitter voltage | C-E short-circuited | ± 20 | V |
| I_C | Collector current | DC, $T_C=104\text{ }^{\circ}\text{C}$ (Note2, 4) | 225 | A |
| I_{CRM} | | Pulse, Repetitive (Note3) | 450 | |
| P_{tot} | Total power dissipation | $T_C=25\text{ }^{\circ}\text{C}$ (Note2, 4) | 1440 | W |
| I_E (Note1) | Emitter current | DC (Note2) | 225 | A |
| I_{ERM} (Note1) | | Pulse, Repetitive (Note3) | 450 | |

MODULE

| Symbol | Item | Conditions | Rating | Unit |
|-------------|--------------------------------|---|------------|--------------------|
| V_{isol} | Isolation voltage | Terminals to base plate, RMS, f=60 Hz, AC 1 min | 4000 | V |
| T_{vjmax} | Maximum junction temperature | Instantaneous event (overload) | 175 | $^{\circ}\text{C}$ |
| T_{Cmax} | Maximum case temperature | (Note4) | 125 | |
| T_{vjop} | Operating junction temperature | Continuous operation (under switching) | -40 ~ +150 | $^{\circ}\text{C}$ |
| T_{stg} | Storage temperature | - | -40 ~ +125 | |

ELECTRICAL CHARACTERISTICS ($T_{vj}=25\text{ }^{\circ}\text{C}$, unless otherwise specified)

INVERTER PART IGBT/FWD

| Symbol | Item | Conditions | Limits | | | Unit | |
|-----------------------------|--------------------------------------|--|--------------------------------------|------|------|---------------|---|
| | | | Min. | Typ. | Max. | | |
| I_{CES} | Collector-emitter cut-off current | $V_{CE}=V_{CES}$, G-E short-circuited | - | - | 1.0 | mA | |
| I_{GES} | Gate-emitter leakage current | $V_{GE}=V_{GES}$, C-E short-circuited | - | - | 0.5 | μA | |
| $V_{GE(th)}$ | Gate-emitter threshold voltage | $I_C=22.5\text{ mA}$, $V_{CE}=10\text{ V}$ | 5.4 | 6.0 | 6.6 | V | |
| V_{CEsat} (Terminal) | Collector-emitter saturation voltage | $I_C=225\text{ A}$, $V_{GE}=15\text{ V}$, Refer to the figure of test circuit (Note5) | $T_{vj}=25\text{ }^{\circ}\text{C}$ | - | 2.00 | 2.40 | V |
| | | | $T_{vj}=125\text{ }^{\circ}\text{C}$ | - | 2.40 | - | |
| | | | $T_{vj}=150\text{ }^{\circ}\text{C}$ | - | 2.50 | - | |
| V_{CEsat} (Chip) | | $I_C=225\text{ A}$, $V_{GE}=15\text{ V}$, (Note5) | $T_{vj}=25\text{ }^{\circ}\text{C}$ | - | 1.95 | 2.35 | V |
| | | | $T_{vj}=125\text{ }^{\circ}\text{C}$ | - | 2.35 | - | |
| | | | $T_{vj}=150\text{ }^{\circ}\text{C}$ | - | 2.45 | - | |
| C_{ies} | Input capacitance | $V_{CE}=10\text{ V}$, G-E short-circuited | - | - | 60 | nF | |
| C_{oes} | Output capacitance | | - | - | 1.6 | | |
| C_{res} | Reverse transfer capacitance | | - | - | 0.5 | | |
| Q_G | Gate charge | $V_{CC}=1000\text{ V}$, $I_C=225\text{ A}$, $V_{GE}=15\text{ V}$ | - | 1.76 | - | μC | |
| $t_{d(on)}$ | Turn-on delay time | $V_{CC}=1000\text{ V}$, $I_C=225\text{ A}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0\text{ }\Omega$, Inductive load | - | - | 800 | ns | |
| t_r | Rise time | | - | - | 200 | | |
| $t_{d(off)}$ | Turn-off delay time | | - | - | 800 | | |
| t_f | Fall time | | - | - | 600 | | |
| V_{EC} (Terminal) (Note1) | Emitter-collector voltage | $I_E=225\text{ A}$, G-E short-circuited, Refer to the figure of test circuit (Note5) | $T_{vj}=25\text{ }^{\circ}\text{C}$ | - | 2.70 | 3.30 | V |
| | | | $T_{vj}=125\text{ }^{\circ}\text{C}$ | - | 2.90 | - | |
| | | | $T_{vj}=150\text{ }^{\circ}\text{C}$ | - | 2.90 | - | |
| V_{EC} (Chip) (Note1) | | $I_E=225\text{ A}$, G-E short-circuited, (Note5) | $T_{vj}=25\text{ }^{\circ}\text{C}$ | - | 2.65 | 3.25 | V |
| | | | $T_{vj}=125\text{ }^{\circ}\text{C}$ | - | 2.75 | - | |
| | | | $T_{vj}=150\text{ }^{\circ}\text{C}$ | - | 2.75 | - | |
| t_{rr} (Note1) | Reverse recovery time | $V_{CC}=1000\text{ V}$, $I_E=225\text{ A}$, $V_{GE}=\pm 15\text{ V}$, | - | - | 300 | ns | |
| Q_{rr} (Note1) | Reverse recovery charge | $R_G=0\text{ }\Omega$, Inductive load | - | 10.2 | - | μC | |
| E_{on} | Turn-on switching energy per pulse | $V_{CC}=1000\text{ V}$, $I_C=I_E=225\text{ A}$, | - | 51.5 | - | mJ | |
| E_{off} | Turn-off switching energy per pulse | $V_{GE}=\pm 15\text{ V}$, $R_G=0\text{ }\Omega$, $T_{vj}=150\text{ }^{\circ}\text{C}$, | - | 56.4 | - | | |
| E_{rr} (Note1) | Reverse recovery energy per pulse | Inductive load | - | 29.0 | - | mJ | |
| $R_{CC'+EE'}$ | Internal lead resistance | Main terminals-chip, per switch, $T_C=25\text{ }^{\circ}\text{C}$ (Note4) | - | 0.94 | - | m Ω | |
| r_g | Internal gate resistance | Per switch | - | 3.3 | - | Ω | |

CM225DX-34T/CM225DXP-34T

HIGH POWER SWITCHING USE
INSULATED TYPE

ELECTRICAL CHARACTERISTICS (cont.; T_{vj}=25 °C, unless otherwise specified) NTC THERMISTOR PART

| Symbol | Item | Conditions | Limits | | | Unit |
|----------------------|-------------------------|---|--------|------|------|------|
| | | | Min. | Typ. | Max. | |
| R ₂₅ | Zero-power resistance | T _C =25 °C (Note4) | 4.85 | 5.00 | 5.15 | kΩ |
| ΔR/R | Deviation of resistance | R ₁₀₀ =493 Ω, T _C =100 °C (Note4) | -7.3 | - | +7.8 | % |
| B _(25/50) | B-constant | Approximate by equation (Note6) | - | 3375 | - | K |
| P ₂₅ | Power dissipation | T _C =25 °C (Note4) | - | - | 10 | mW |

THERMAL RESISTANCE CHARACTERISTICS

| Symbol | Item | Conditions | Limits | | | Unit |
|-----------------------|----------------------------|---|--------|------|------|------|
| | | | Min. | Typ. | Max. | |
| R _{th(j-c)Q} | Thermal resistance | Junction to case, per Inverter IGBT (Note4) | - | - | 104 | K/kW |
| R _{th(j-c)D} | | Junction to case, per Inverter FWD (Note4) | - | - | 176 | |
| R _{th(c-s)} | Contact thermal resistance | Case to heat sink, Thermal grease applied (Note4, 7) per 1 module, PC-TIM applied (Note4, 8) | - | 11.5 | - | K/kW |
| | | | - | 3.1 | - | |

MECHANICAL CHARACTERISTICS

| Symbol | Item | Conditions | Limits | | | Unit | |
|----------------|------------------------|---------------------------------|------------------------|------|------|------|----|
| | | | Min. | Typ. | Max. | | |
| M _t | Mounting torque | Main terminals M 6 screw | 3.5 | 4.0 | 4.5 | N·m | |
| M _s | Mounting torque | Mounting to heat sink M 5 screw | 2.5 | 3.0 | 3.5 | N·m | |
| d _s | Creepage distance | Solder pin type (DX) | Terminal to terminal | 17 | - | - | mm |
| | | | Terminal to base plate | 18.1 | - | - | |
| | | Pressfit pin type (DXP) | Terminal to terminal | 17 | - | - | mm |
| | | | Terminal to base plate | 18.6 | - | - | |
| d _a | Clearance | Solder pin type (DX) | Terminal to terminal | 10 | - | - | mm |
| | | | Terminal to base plate | 16.2 | - | - | |
| | | Pressfit pin type (DXP) | Terminal to terminal | 10 | - | - | mm |
| | | | Terminal to base plate | 16.2 | - | - | |
| e _c | Flatness of base plate | On the centerline X, Y (Note9) | ±0 | - | +200 | μm | |
| m | mass | - | - | 300 | - | g | |

*: This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU.

Note1. Represent ratings and characteristics of the anti-parallel, emitter-collector free-wheeling diode (FWD).

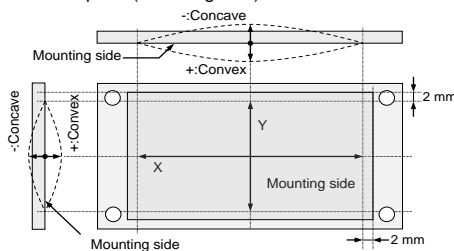
- Junction temperature (T_{vj}) should not increase beyond T_{vjmax} rating.
- Pulse width and repetition rate should be such that the device junction temperature (T_{vj}) dose not exceed T_{vjmax} rating.
- Case temperature (T_C) and heat sink temperature (T_S) are defined on the each surface (mounting side) of base plate and heat sink just under the chips.
Refer to the figure of chip location.
- Pulse width and repetition rate should be such as to cause negligible temperature rise. Refer to the figure of test circuit.

$$6. B_{(25/50)} = \ln\left(\frac{R_{25}}{R_{50}}\right) / \left(\frac{1}{T_{25}} - \frac{1}{T_{50}}\right)$$

R₂₅: resistance at absolute temperature T₂₅ [K]; T₂₅=25 [°C]+273.15=298.15 [K]

R₅₀: resistance at absolute temperature T₅₀ [K]; T₅₀=50 [°C]+273.15=323.15 [K]

- Typical value is measured by using thermally conductive grease of λ=0.9 W/(m·K)/D_(c-s)=50 μm.
- Typical value is measured by using PC-TIM of λ=3.4 W/(m·K)/D_(c-s)=50 μm.
- The base plate (mounting side) flatness measurement points (X, Y) are shown in the following figure.



CM225DX-34T/CM225DXP-34T

HIGH POWER SWITCHING USE

INSULATED TYPE

Note10. Use the following screws when mounting the printed circuit board (PCB) on the standoffs.

PCB thickness : t1.6

| Type | Manufacturer | Size | Tightening torque (N·m) | Recommended tightening method |
|----------------------|--------------|--------------------|-------------------------|--|
| (1) PT® | EJOT | K25×8 | 0.55 ± 0.055 | by handwork (equivalent to 30 rpm by mechanical screw driver) ~ 600 rpm (by mechanical screw driver) |
| (2) PT® | | K25×10 | 0.75 ± 0.075 N·m | |
| (3) DELTA PT® | | 25×8 | 0.55 ± 0.055 N·m | |
| (4) DELTA PT® | | 25×10 | 0.75 ± 0.075 N·m | |
| (5) B1 tapping screw | - | φ2.6×10 φ2.6×12 | 0.75 ± 0.075 N·m | |

RECOMMENDED OPERATING CONDITIONS

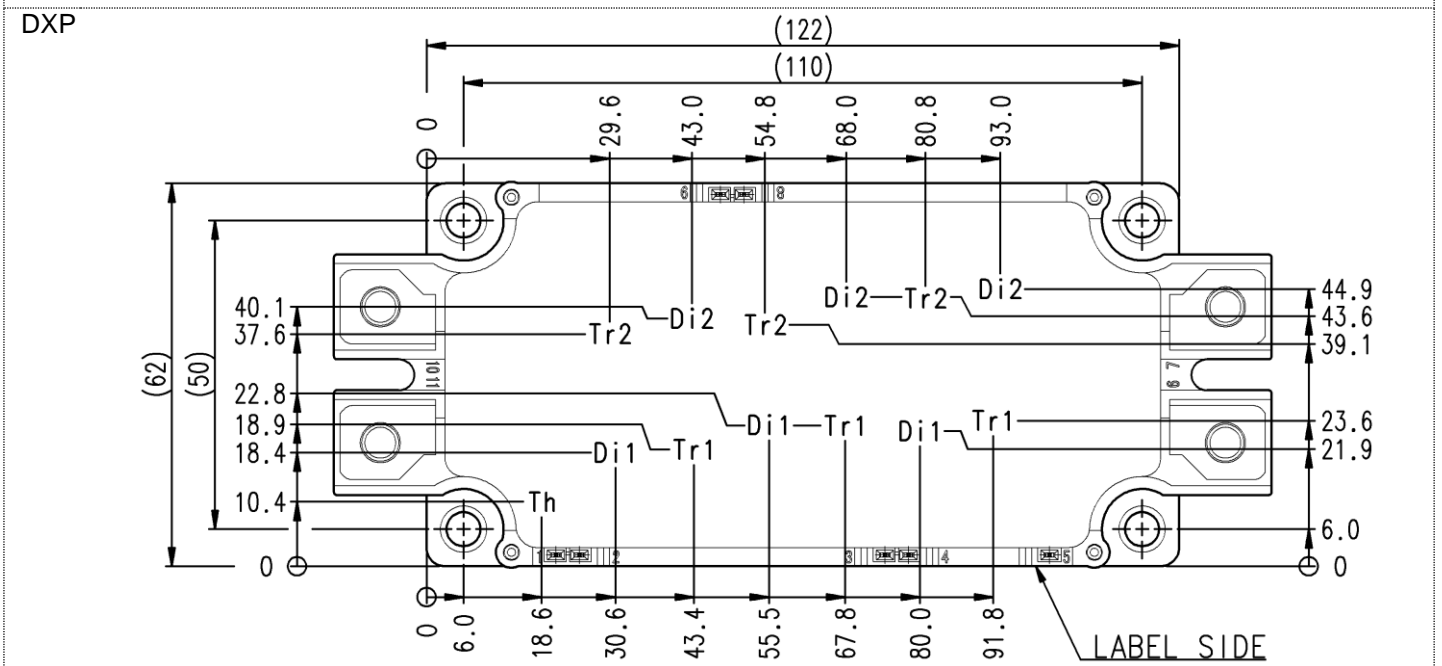
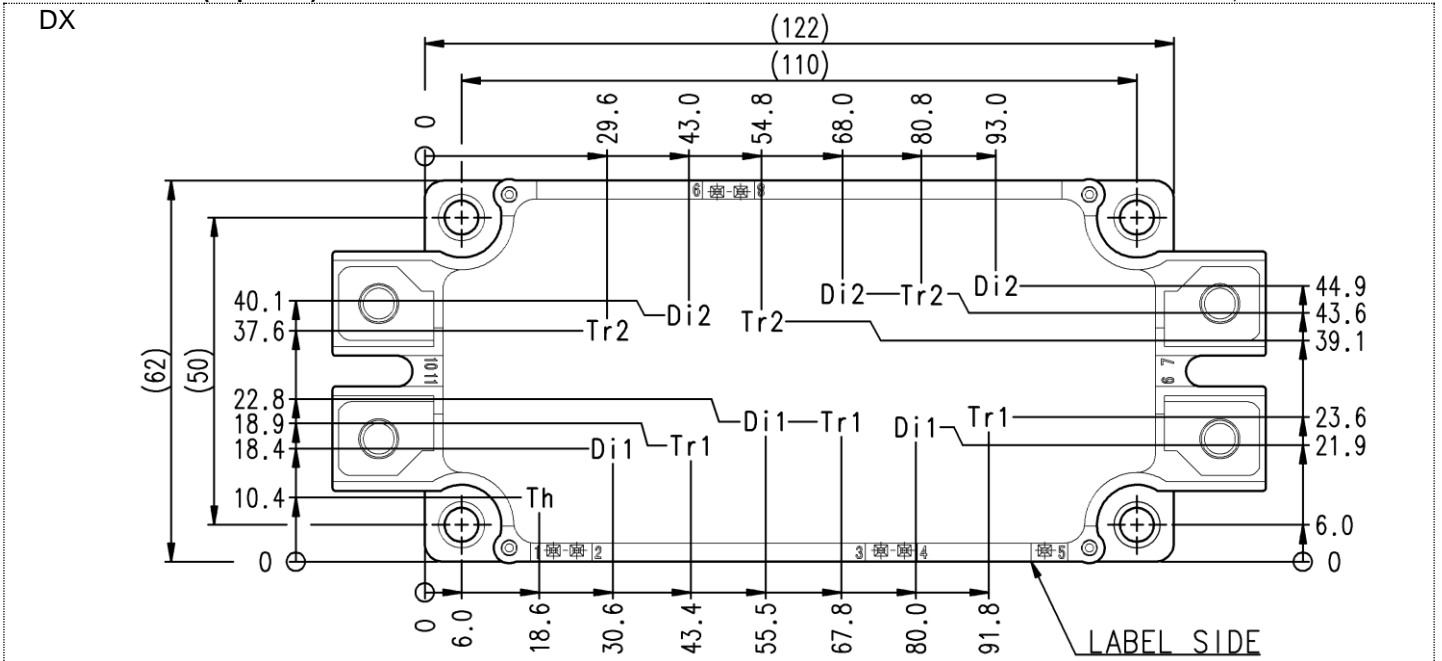
| Symbol | Item | Conditions | Limits | | | Unit |
|------------|-------------------------------|--|--------|------|------|------|
| | | | Min. | Typ. | Max. | |
| V_{CC} | (DC) Supply voltage | Applied across C1-E2 terminals | - | 1000 | 1200 | V |
| V_{GEon} | Gate (-emitter drive) voltage | Applied across G1-Es1/G2-Es2 terminals | 13.5 | 15.0 | 16.5 | V |
| R_G | External gate resistance | Per switch | 0 | - | 30 | Ω |

CM225DX-34T/CM225DXP-34T

HIGH POWER SWITCHING USE
INSULATED TYPE

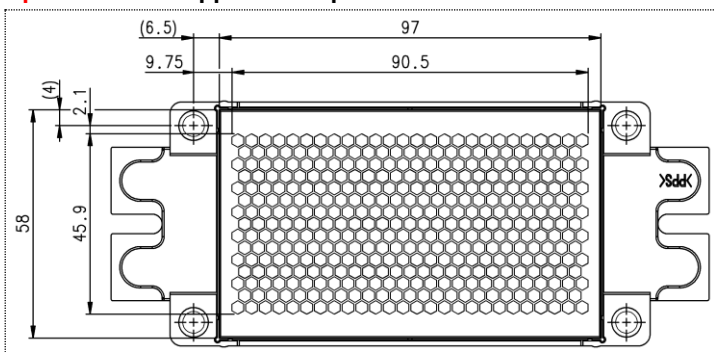
CHIP LOCATION (Top view)

Dimension in mm, tolerance: ± 1 mm



Tr1/Tr2: IGBT, Di1/Di2: FWD, Th: NTC thermistor

Option: PC-TIM applied baseplate outline

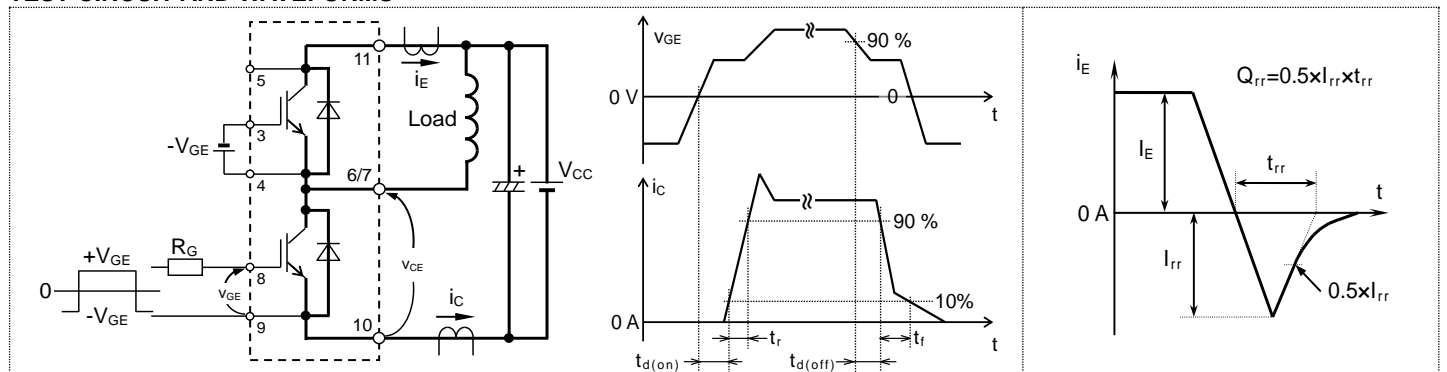


CM225DX-34T/CM225DXP-34T

HIGH POWER SWITCHING USE

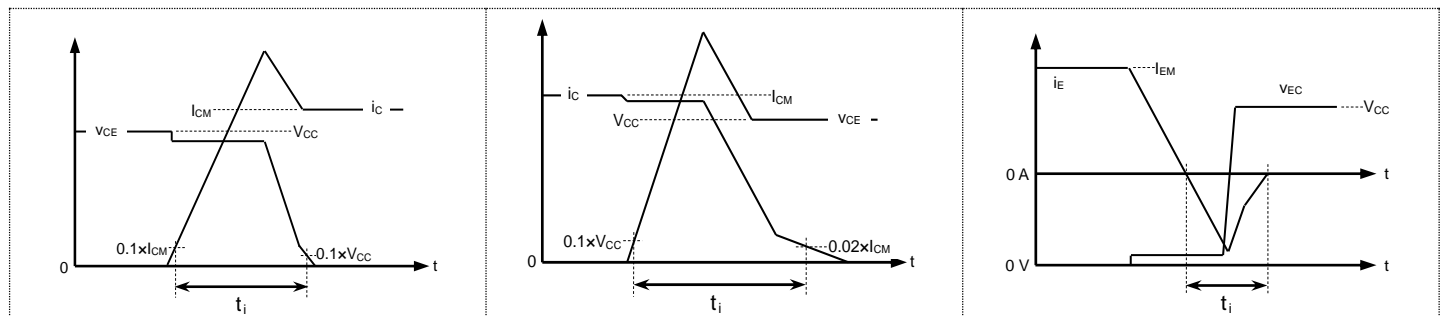
INSULATED TYPE

TEST CIRCUIT AND WAVEFORMS



Switching characteristics test circuit and waveforms

t_{rr} , Q_{rr} characteristics test waveform



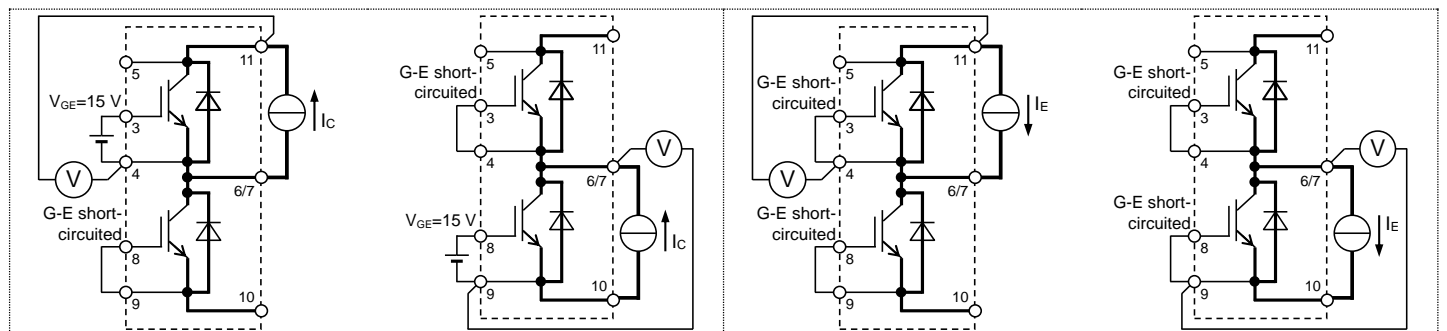
IGBT Turn-on switching energy

IGBT Turn-off switching energy

FWD Reverse recovery energy

Switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

TEST CIRCUIT



Tr1

Tr2

Di1

Di2

V_{CEsat} characteristics test circuit

V_{EC} characteristics test circuit

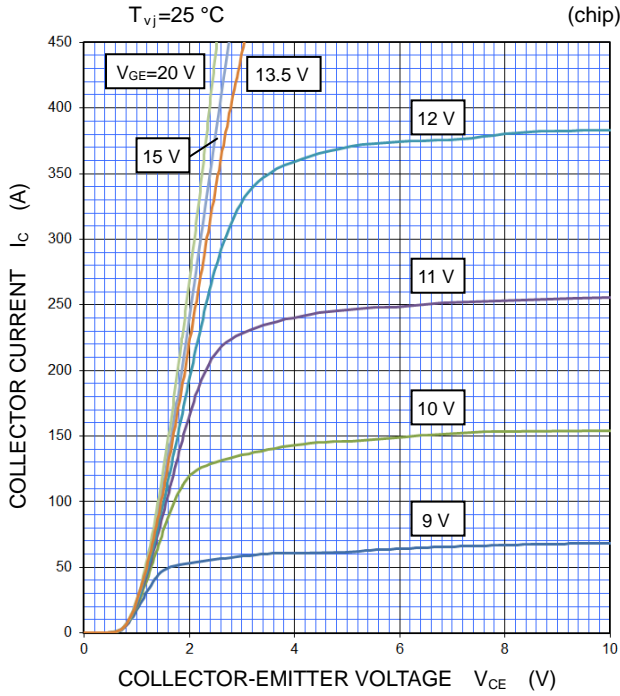
CM225DX-34T/CM225DXP-34T

HIGH POWER SWITCHING USE
INSULATED TYPE

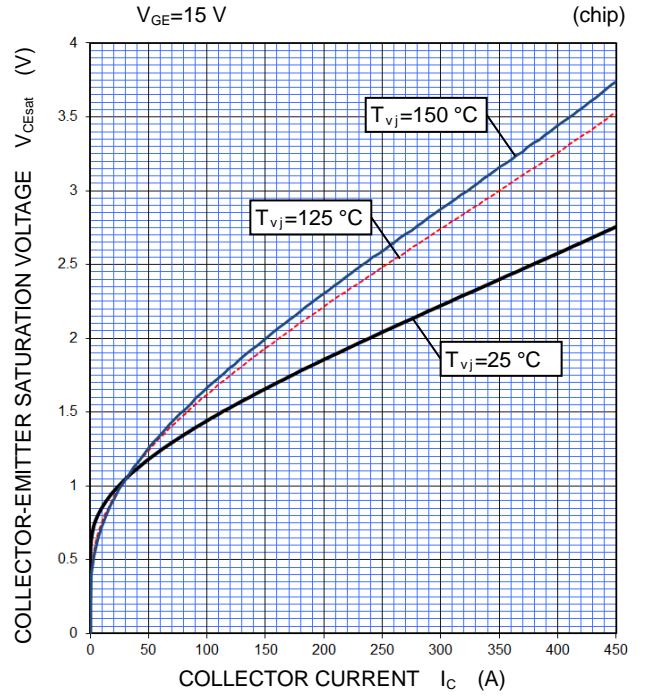
PERFORMANCE CURVES

INVERTER PART

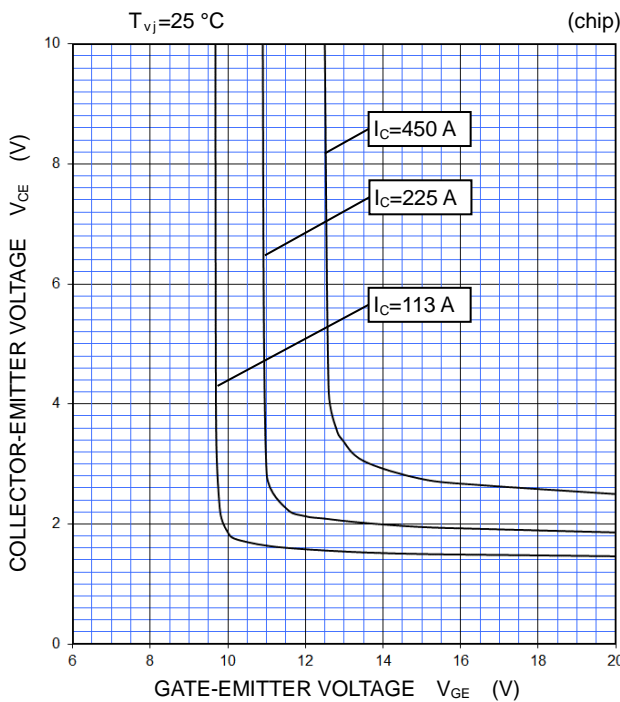
OUTPUT CHARACTERISTICS
(TYPICAL)



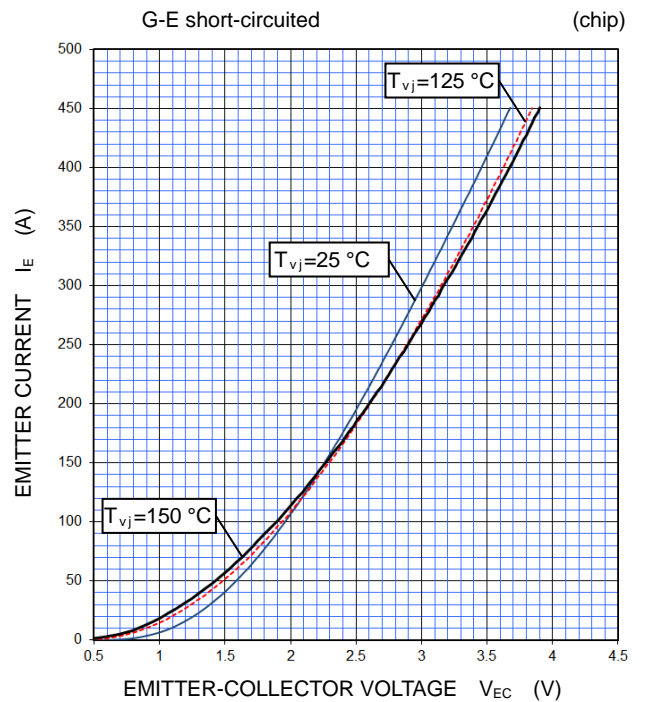
COLLECTOR-EMITTER SATURATION VOLTAGE
CHARACTERISTICS
(TYPICAL)



COLLECTOR-EMITTER VOLTAGE CHARACTERISTICS
(TYPICAL)



FREE WHEELING DIODE
FORWARD CHARACTERISTICS
(TYPICAL)



CM225DX-34T/CM225DXP-34T

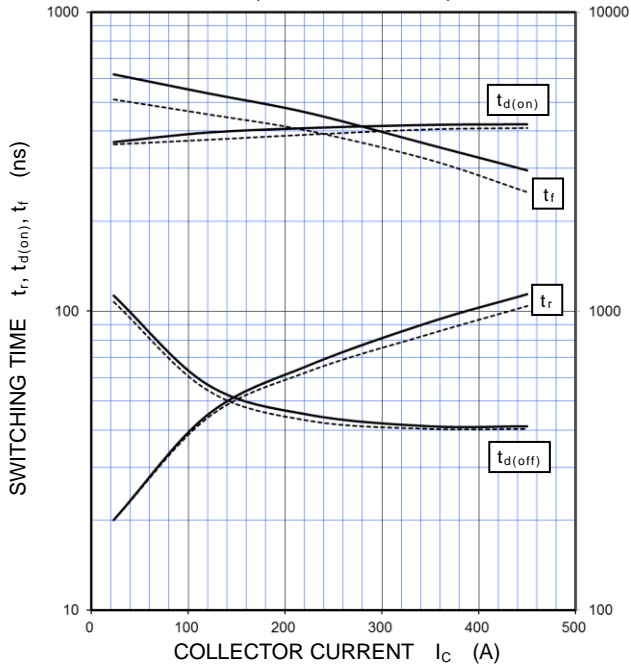
HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

INVERTER PART

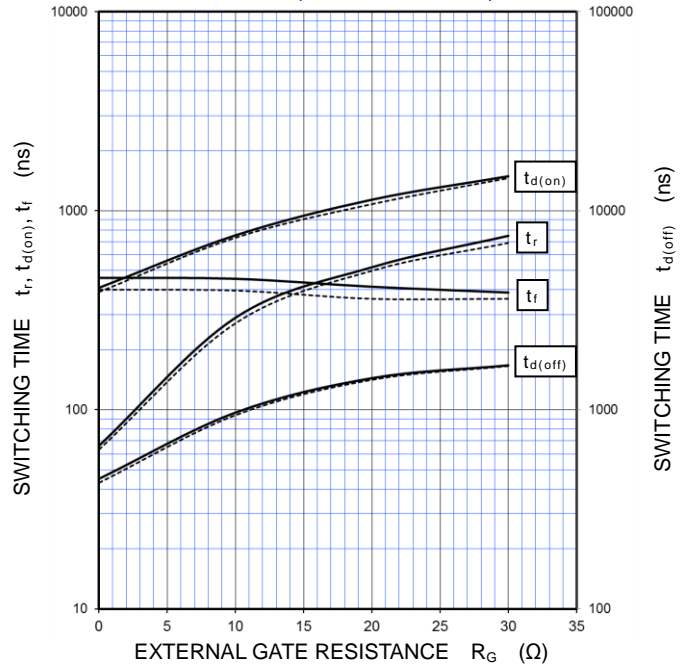
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=1000\text{ V}$, $R_G=0\ \Omega$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$



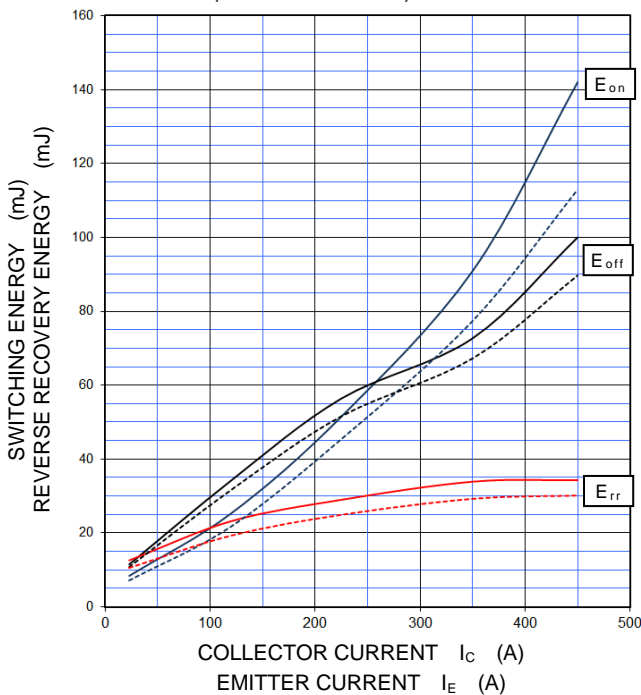
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=1000\text{ V}$, $I_C=225\text{ A}$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$



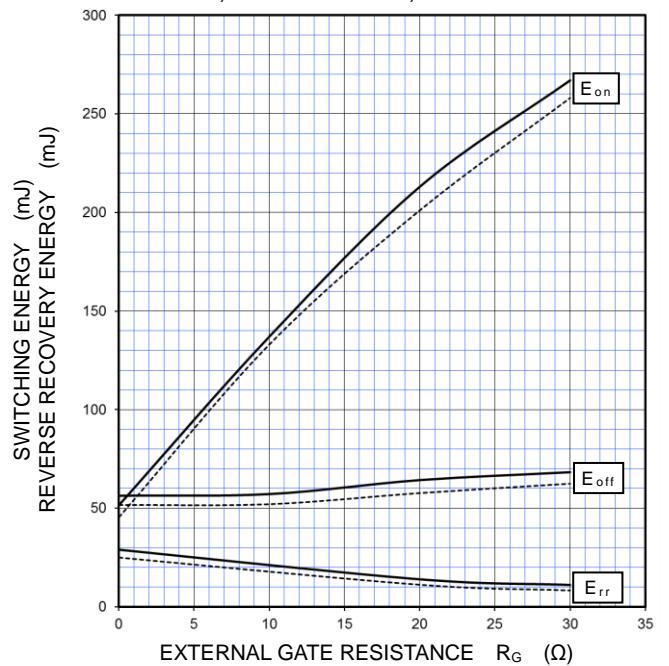
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=1000\text{ V}$, $R_G=0\ \Omega$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD, PER PULSE
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$



HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=1000\text{ V}$, $I_C/I_E=225\text{ A}$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD, PER PULSE
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$



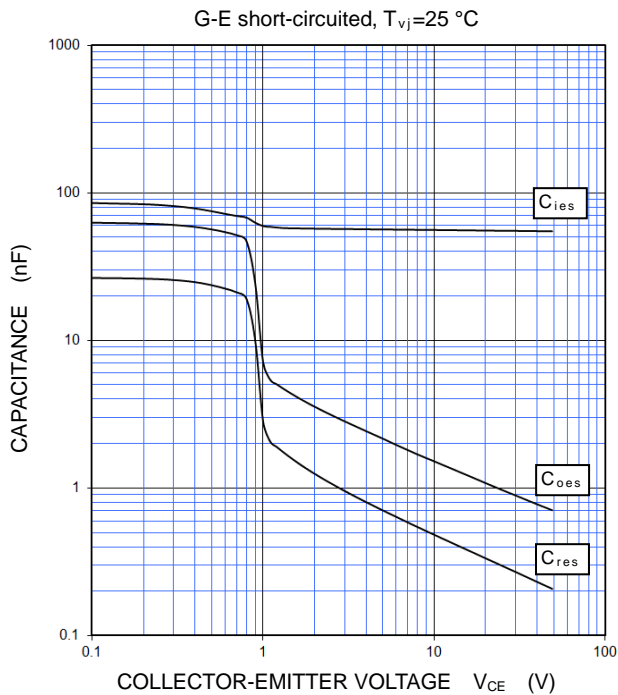
CM225DX-34T/CM225DXP-34T

HIGH POWER SWITCHING USE
INSULATED TYPE

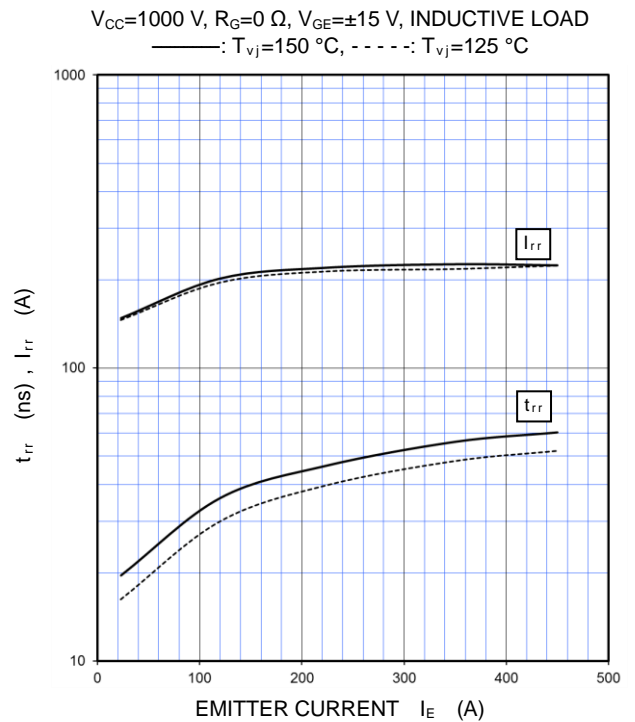
PERFORMANCE CURVES

INVERTER PART

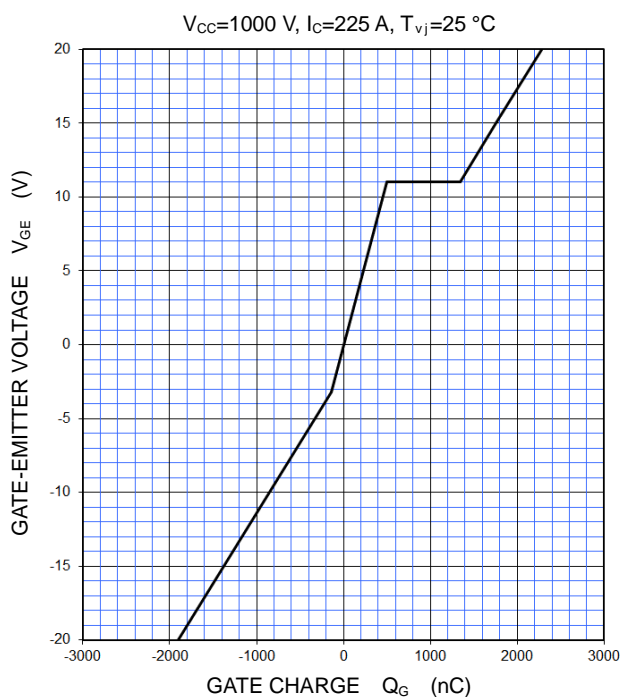
CAPACITANCE CHARACTERISTICS (TYPICAL)



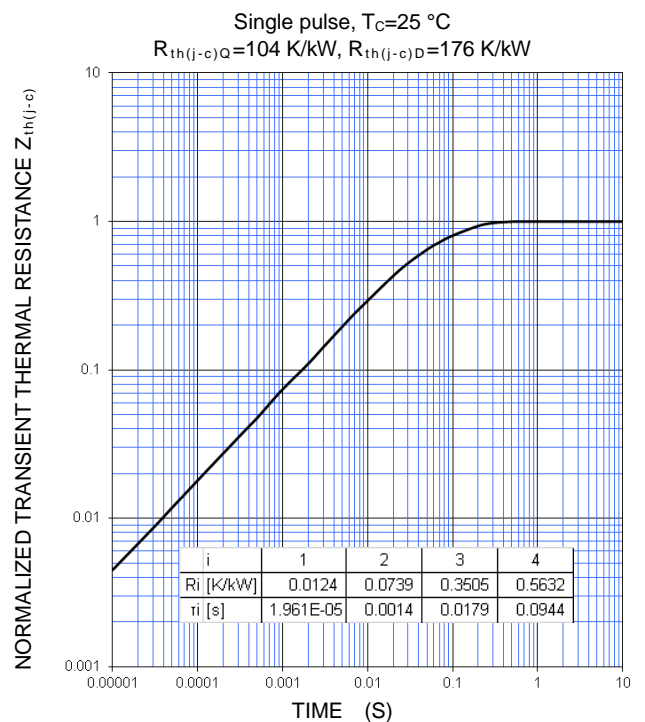
FREE WHEELING DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



GATE CHARGE CHARACTERISTICS (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (MAXIMUM)



CM225DX-34T/CM225DXP-34T

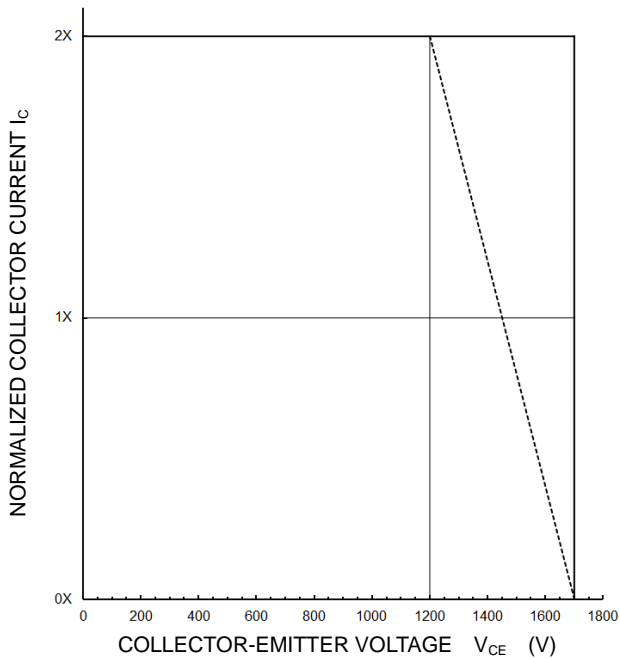
HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

INVERTER PART

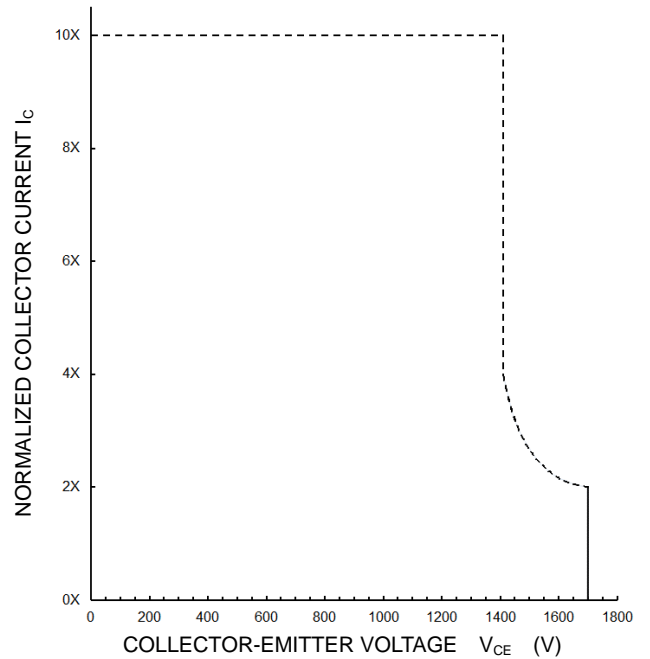
**TURN-OFF SWITCHING SAFE OPERATING AREA
(REVERSE BIAS SAFE OPERATING AREA)
(MAXIMUM)**

$V_{CC} \leq 1200 \text{ V}$, $R_G = 0 \sim 30 \ \Omega$, $V_{GE} = \pm 15 \text{ V}$,
 ———: $T_{vj} = 25 \sim 150 \text{ }^\circ\text{C}$ (Normal load operations (Continuous))
 - - - - -: $T_{vj} = 175 \text{ }^\circ\text{C}$ (Unusual load operations (Limited period))



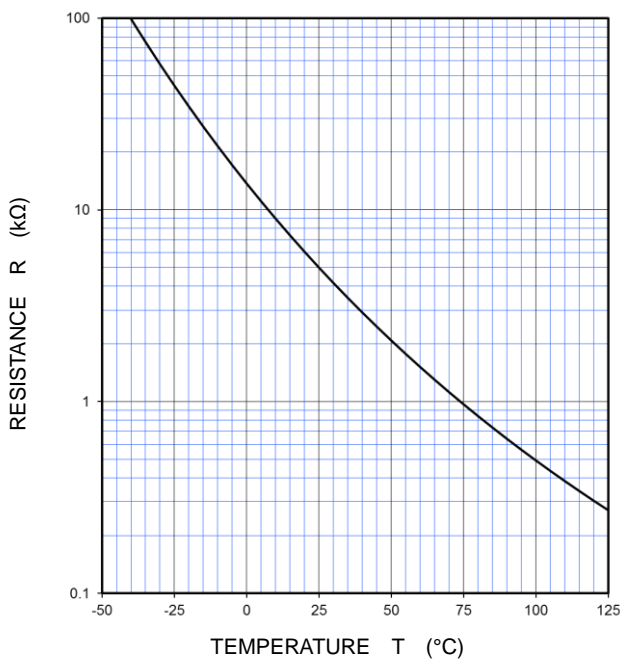
**SHORT-CIRCUIT SAFE OPERATING AREA
(MAXIMUM)**

$V_{CC} \leq 1200 \text{ V}$, $R_G = 0 \sim 30 \ \Omega$, $V_{GE} = \pm 15 \text{ V}$,
 $T_{vj} = 25 \sim 150 \text{ }^\circ\text{C}$, $t_w \leq 8 \ \mu\text{s}$, Non-Repetitive



NTC thermistor part

**TEMPERATURE CHARACTERISTICS
(TYPICAL)**



Note: The characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Keep safety first in your circuit designs!

This product is designed for industrial application purpose. The performance, the quality and support level of the product is guaranteed by "Customer's Std. Spec."

Mitsubishi Electric Corporation puts its reasonable effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them by the reliability lifetime such as Power Cycle, Thermal Cycle or others, or to be used under special circumstances (e.g. high humidity, dusty, salty, highlands, environment with lots of organic matter / corrosive gas / explosive gas, or situation which terminal of semiconductor products is received strong mechanical stress).

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